

High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = 140 V
- Complementary to 2STW1695
- Fast-switching speed
- Typical f_t = 20 MHz
- Fully characterized at 125 °C

Applications

■ Audio power amplifier

Description

The device is a NPN transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour. Recommended for 70 W to 100 W high fidelity audio frequency amplifier output stage.

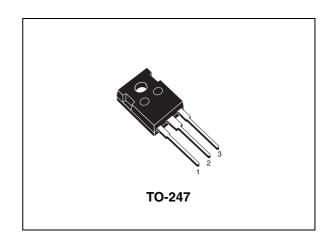


Figure 1. Internal schematic diagram

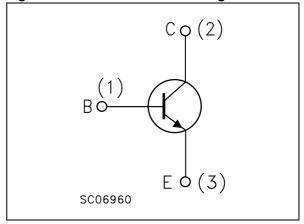


Table 1. Device summary

Order code	Marking	Package	Packaging	
2STW4468	2STW4468	TO-247	Tube	

Electrical ratings 2STW4468

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	200	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	140	V
V _{EBO}	Emitter-base voltage (I _C = 0)	6	V
I _C	Collector current	10	Α
I _{CM}	Collector peak current (t _P < 5 ms)	20	Α
P _{tot}	Total dissipation at T _c = 25 °C	100	W
T _{stg}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	1.25	°C/W

2STW4468 Electrical characteristics

2 Electrical characteristics

($T_{case} = 25 \, ^{\circ}C$; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 200 V			0.1	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 6 V			0.1	μΑ
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = 50 mA	140			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = 100 μA	200			V
V _{(BR)EBO (1)}	Emitter-base breakdown voltage (I _C = 0)	I _E = 1 mA	6			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = 5 A$ $I_B = 50$ $I_C = 7 A$ $I_B = 70$			0.5 0.7	V V
V _{BE}	Base-emitter voltage	$V_{CE} = 5 V$ $I_C = 5 A$	1		1.3	V
h _{FE}	DC current gain	$I_C = 3 A$ $V_{CE} = 4$ $I_C = 5 A$ $V_{CE} = 4$			140	
f _T	Transition frequency	I _C = 0.5 A V _{CE} = 1	2 V	20		MHz
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = 10 V f = 1 M	lHz	150		pF
	Resistive Load					
t _{on}	Turn-on time	$V_{CC} = 60 \text{ V}$ $I_C = 5 \text{ A}$	١	0.22		μs
t _{stg}	Storage time	$I_{B1} = -I_{B2} = 0.5 A$		4.3		μs
t _f	Fall time			0.5		μs

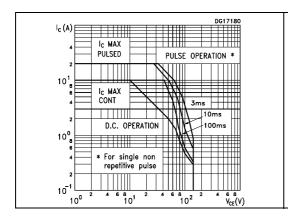
^{1.} Pulse duration = 300 $\mu s,$ duty cycle \leq 1.5 %

Electrical characteristics 2STW4468

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Output characteristics



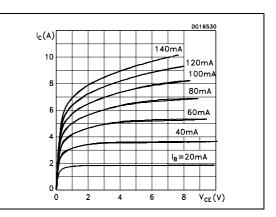
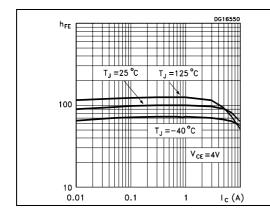


Figure 4. DC current gain

Figure 5. Collector-emitter saturation voltage



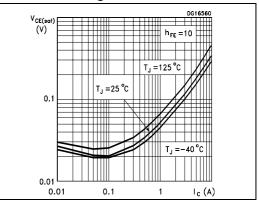
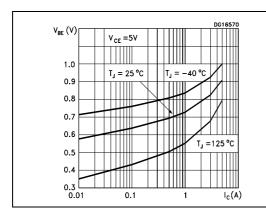
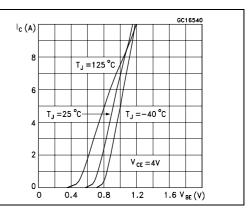


Figure 6. Base-emitter voltage

Figure 7. Base-emitter voltage

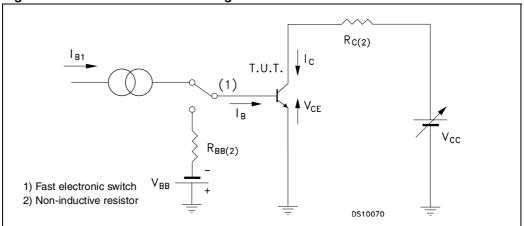




2STW4468 Electrical characteristics

2.2 Test circuit

Figure 8. Resistive load switching test circuit

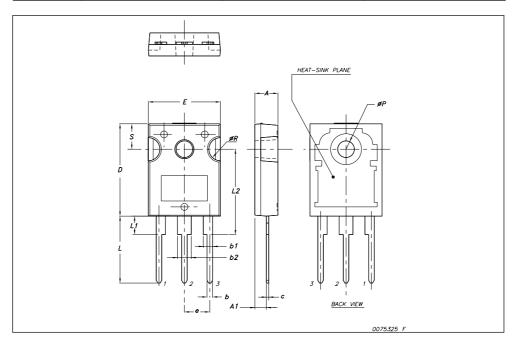


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TΩ	247	Mac	shan	ical	data
1 ().	-/4/	IVIEC	nan	ucai	nata

Dim.	mm.				
	Min.	Тур	Max.		
Α	4.85		5.15		
A1	2.20		2.60		
b	1.0		1.40		
b1	2.0		2.40		
b2	3.0		3.40		
С	0.40		0.80		
D	19.85		20.15		
E	15.45		15.75		
е		5.45			
L	14.20		14.80		
L1	3.70		4.30		
L2		18.50			
øΡ	3.55		3.65		
øR	4.50		5.50		
S		5.50			



Revision history 2STW4468

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
23-Oct-2006	1	Initial release
09-Feb-2007	2	New graphics
20-Feb-2007	3	Document status promoted from preliminary data to datasheet.
13-Oct-2008	4	Content reworked to improve readability, no technical changes.

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